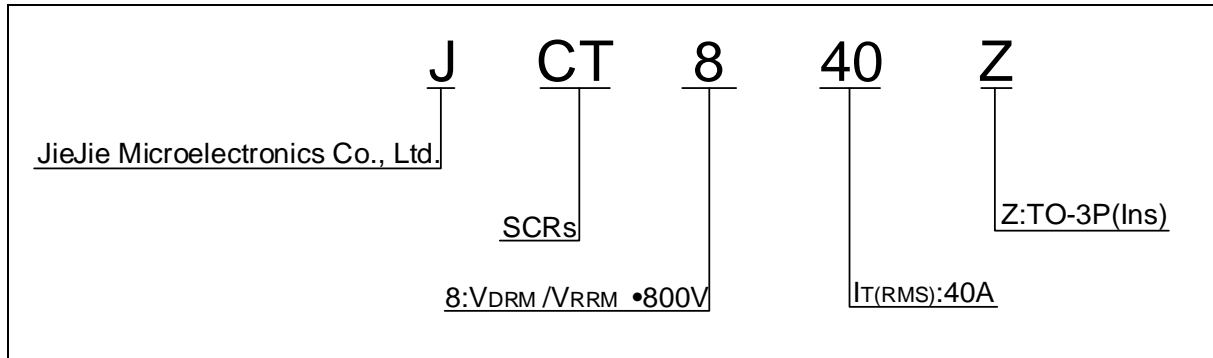




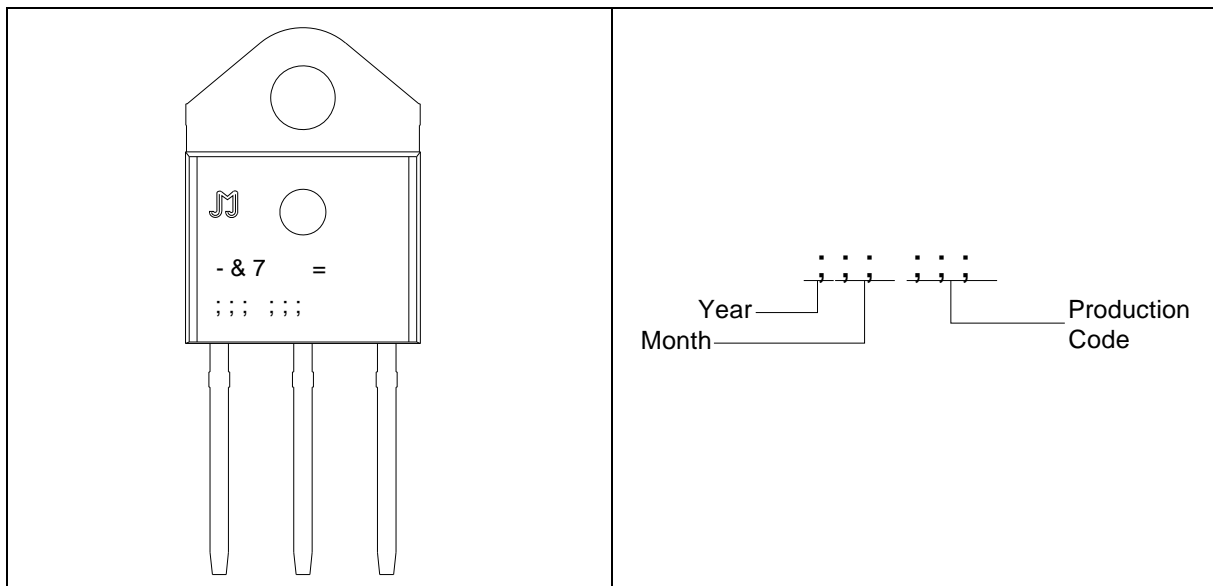
# JCT840Z

Peak gate current ( $t_p=20\mu s$ , $T_j=125$ )	$I_{GM}$	10	A
Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	20	W
Peak pulse voltage ( $T_j=25$			

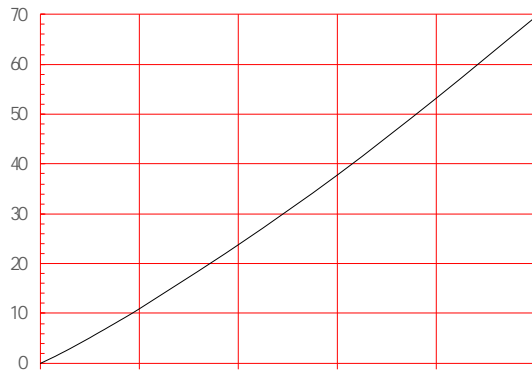
ORDERING INFORMATION



MARKING

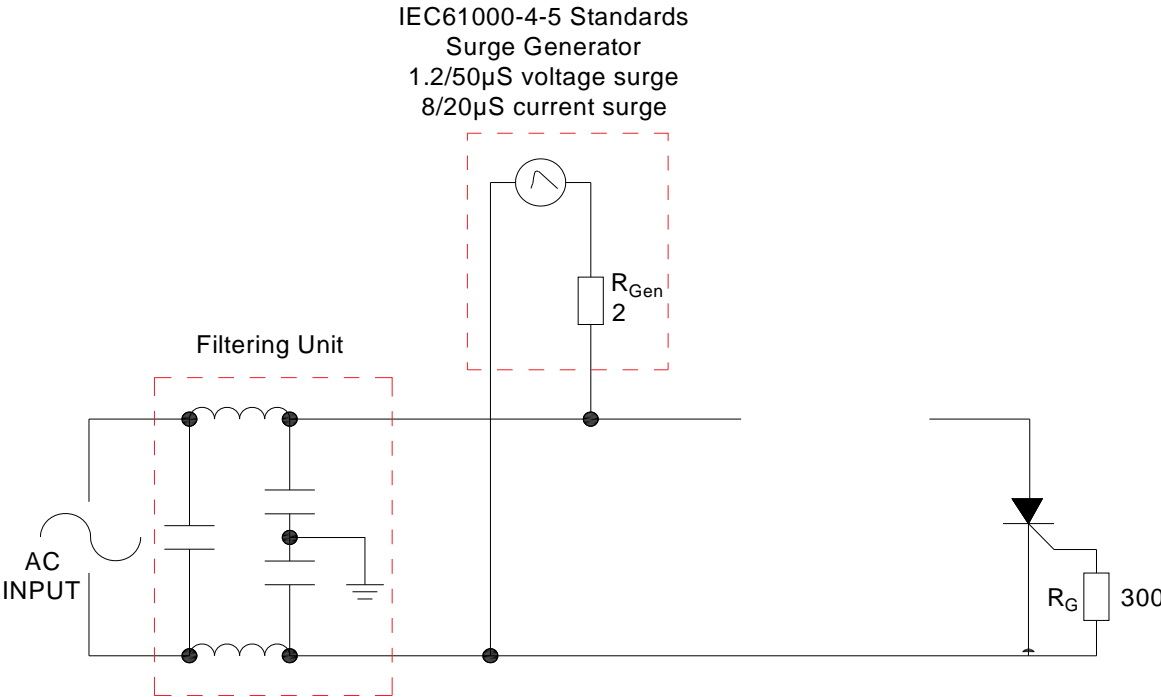


**FIG.1:** Maximum power dissipation versus RMS on-state current



**FIG.2:** RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



**ORDERING INFORMATION**

<b>Order code</b>	<b>Voltage V<sub>DRM</sub>/V<sub>RRM</sub> (V)</b>	<b>IGT(mA)</b>	<b>Package</b>	<b>Base qty. (pcs)</b>	<b>Delivery mode</b>
<b>JCT840Z</b>	<b>800</b>	<b>35</b>	<b>TO-3P(Ins)</b>	<b>30</b>	<b>Tube</b>

**Document Revision History**

<b>Date</b>	<b>Revision</b>	<b>Changes</b>
Apr.13, 2023	A.1.0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA



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